

BYV410-600 Dual enhanced ultrafast power diode Rev. 2 – 5 August 2011

Product data sheet

Product profile 1.

1.1 General description

Dual enhanced ultrafast power diode in a SOT78 (TO-220AB) plastic package.

1.2 Features and benefits

- High thermal cycling performance
- Low on state losses

1.3 Applications

- Dual mode (DCM and CCM) PFC
- Low thermal resistance
- Soft recovery characteristic minimizes power consuming oscillations
- Power Factor Correction (PFC) for Interleaved Topology

1.4 Quick reference data

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{RRM}	repetitive peak reverse voltage		-	-	600	V
I _{O(AV)}	average output current	square-wave pulse; $\delta = 0.5$; $T_{mb} \le 92$ °C; both diodes conducting; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	-	20	A
Static cha	aracteristics					
V _F	forward voltage	I _F = 10 A; T _j = 150 °C	-	1.3	1.9	V
		$I_F = 10 \text{ A}; T_j = 25 \text{ °C};$ see Figure 4	-	1.4	2.1	V
Dynamic	characteristics					
t _{rr}	reverse recovery time	I _F = 1 A; V _R = 30 V; dI _F /dt = 100 A/μs; T _j = 25 °C; see <u>Figure 5</u>	-	20	35	ns
Q _r	recovered charge	I _F = 1 A; V _R = 30 V; dI _F /dt = 100 A/μs	-	15	28	nC



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2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1		
2	К	cathode	mb	
3	A2	anode 2		к
	К	mounting base; cathode		sym125
			SOT78 (TO-220AB)	

3. Ordering information

Table 3.Ordering information

Type number	Package		
	Name	Description	Version
BYV410-600	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

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4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{RRM}	repetitive peak reverse voltage		-	600	V
V _{RWM}	crest working reverse voltage		-	600	V
V _R	reverse voltage	DC	-	600	V
I _{O(AV)}	average output current	square-wave pulse; $\delta = 0.5$; T _{mb} ≤ 92 °C; both diodes conducting; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	20	A
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 µs; T _{mb} ≤ 108 °C; per diode	-	20	А
I _{FSM}	non-repetitive peak forward current	t _p = 8.3 ms; sine-wave pulse; T _{j(init)} = 25 °C; per diode	-	132	А
		t _p = 10 ms; sine-wave pulse; T _{j(init)} = 25 °C; per diode	-	120	А
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	150	°C

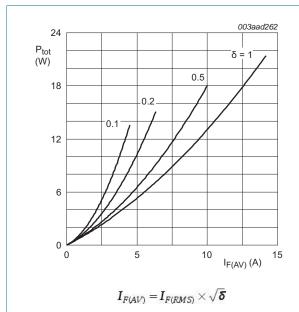
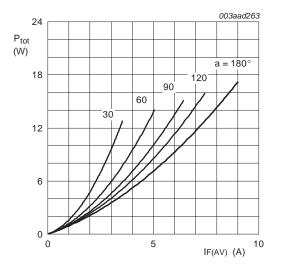


Fig 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



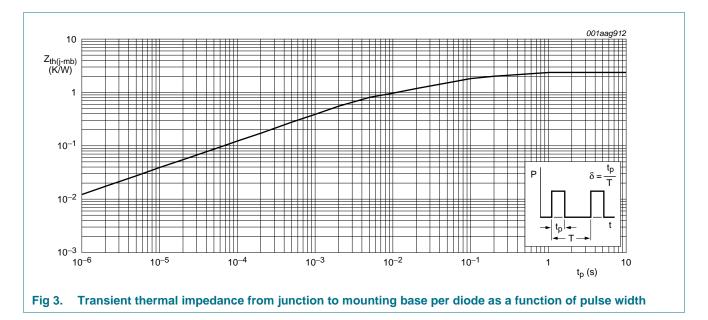
 $a = \text{form factor} = I_{T(RMS)} / I_{T(AV)}$

Fig 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

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5. Thermal characteristics

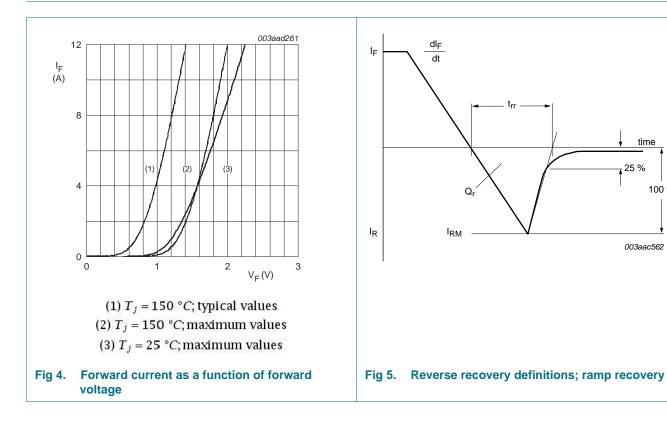
Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	with heatsink compound; per diode; see <u>Figure 3</u>	-	-	2.4	K/W
		with heatsink compound; both diodes conducting	-	-	1.6	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient		-	60	-	K/W



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Characteristics 6.

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics					
V _F	forward voltage	I _F = 10 A; T _j = 150 °C	-	1.3	1.9	V
		I _F = 10 A; T _j = 25 °C; see <u>Figure 4</u>	-	1.4	2.1	V
I _R	reverse current	V _R = 600 V	-	13	50	μA
		$V_{R} = 600 \text{ V}; \text{ T}_{j} = 100 ^{\circ}\text{C}$	-	- 1	1.5	mA
Dynamic	characteristics					
Qr	recovered charge	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A}/\mu\text{s}$	-	15	28	nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A}/\mu\text{s}$; $T_j = 25 \text{ °C}$; see <u>Figure 5</u>	-	20	35	ns
I _{RM}	peak reverse recovery current	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A}/\mu\text{s}$; see Figure 5	-	1.4	1.9	А
V_{FR}	forward recovery voltage	$I_F = 1 \text{ A}; \text{ d}I_F/\text{d}t = 100 \text{ A}/\mu\text{s}; \text{ see } \frac{\text{Figure 6}}{100 \text{ A}}$	-	3.2	-	V



time

003aac562

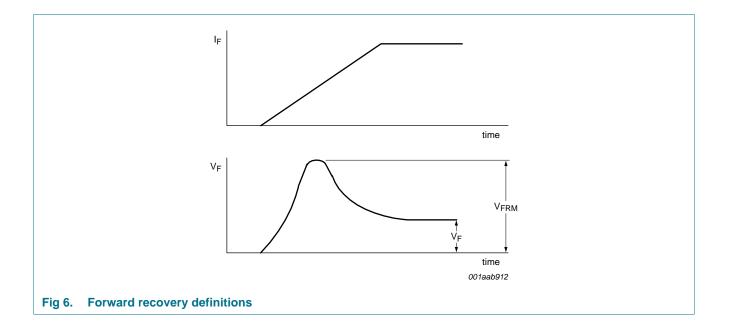
100 %

25 %

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Package outline 7.

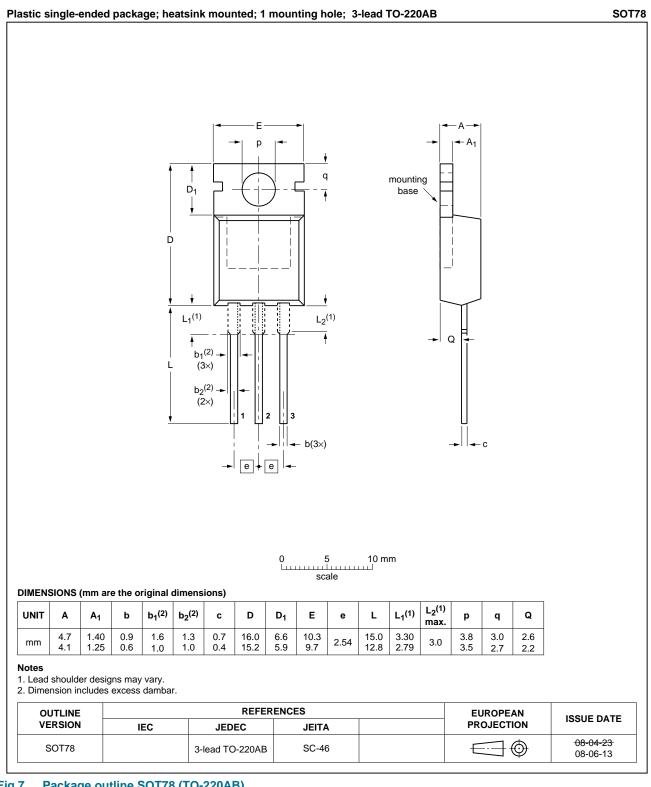


Fig 7. Package outline SOT78 (TO-220AB)

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8. Revision history

Table 7. Revision	n history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BYV410-600 v.2	20110805	Product data sheet	-	BYV410-600_1
Modifications:	 Various chang 	es to content.		
BYV410-600_1	20090629	Product data sheet	-	-

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9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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